

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S23	2689	(438/222,478,479,481).CQLS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/01 13:54
S24	5238	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:56
S25	8595965	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:57
S26	189077	phosphine or phosphorous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 13:59
S27	4879	silane same dichlorosilane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:00
S28	12	S24 same S25 same S26 same S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:00
S29	572907	(form or formed or forming or deposit or depositing or deposited or provide or provided or providing) near8 (Si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:03
S30	11	S28 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:03
S31	47	("4714594").PN. OR ("4846102"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/01 14:07
S32	6	S31 and S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 14:50

S33	5242	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S34	6598224	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S35	189184	phosphine or phosphorous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S36	4887	silane same dichlorosilane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S37	12	S33 same S34 same S35 same S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S38	573286	(form or formed or forming or deposit or depositing or deposited or provide or provided or providing) near8 (Si or silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S39	11	S37 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:51
S40	3926	(438/142,197,299,300).CQLS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 13:52
S41	11	S39 and (S/D or source/drain or source or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 13:53
S42	11	S41 and (phosphine or phosphorous or P or "PH.sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 14:48
S43	1778593	(MOS or MOSFET or transistor or FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 14:57

S44	6988	(switch\$4 or change or changed or changing or alternat\$4 or replace or replaced or replacing) near8 ((inert or Nitrogen or "N.sub.2") near8 (hydrogen or "H.sub.2"))	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:13
S45	148	(S33 and S34 and S35 and S36)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:13
S46	806	(438/300).CQLS.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 15:14
S47	13	S45 and S46	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 15:14
S48	2	("6251188").PN.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 16:27
S49	8	("20030003646" "5378651" "6251188" "6391749").PN.	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 19:11
S50	5242	(epi or epitaxial or epitaxially) near8 (reactor or chamber)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S51	8598224	((inert or carrier) near gas) or Helium or He or Nitrogen or N or "N.sub.2"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S52	189184	phosphine or phosphorous	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S53	4887	silane same dichlorosilane	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09
S54	148	(S50 and S51 and S52 and S53)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:09

S55	37261	(raise or raised or elevate or elevated or elevating) near8 (source or drain or S/D or source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S56	41	S54 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S57	14	S56 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 20:11
S58	237	(Raised near4 (source/drain)) same MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:15
S59	2	S58 and (silane or "SiH.sub.4") and (dichlorosilane or DCS) and (phosphine or phosphorous or "PH.sub.3") and (nitrogen or "N.sub.2" or hydrogen or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:17
S60	103	(("20010001724" "20010009303" "20010031535" "20010045604" "20020019127" "20020048910" "20020052084" "20020056879" "20020063292" "20020190284" "20030113971" "20040007724" "20040014276" "20040014304" "20040070035" "20040084735" "20040119101" "20040142545" "20040173815" "4717681" "4755478" "4803539" "5034348" "5089872" "5198689" "5217923" "5242847" "5334861" "5336903" "5346840" "5442205" "5496750" "5496771" "5659194" "5714777" "5844260" "5847419" "5869359" "5877535" "5891769" "5933741" "5998807" "6008111" "6066563" "6096647" "6107653" "6121100" "6132806" "6133124" "6159856" "6187657" "6214679" "6235575" "6246077" "6251780" "6268257" "6281532" "6291321" "6294448" "6306698" "6313486" "6315384" "6316357" "6319805" "6362071" "6380008" "6399970" "6406986"	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/04 09:20

		"6410371" "6461960" "6486520" "6498359" "6503833" "6509587" "6555839" "6555880" "6562703" "6563152" "6566718" "6573126" "6573160" "6583015" "6593191" "6593641" "6603156" "6605498" "6621131" "6657223" "6682965" "6686617" "6699765" "6703648" "6724019" "6743684").PN. OR ("6946371").URPN.				
S61	10	S60 and (silane or "SH.sub.4") and (dichlorosilane or DCS) and (phosphine or phosphorous or "PH. sub.3") and (nitrogen or "N.sub.2" or hydrogen or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:22
S62	0	(epitaxial near4 reactor4 near chamber) same (mixture near8 (chlorosilane or dichlorosilane or trichlorosilane or tetrachlorosilane or DCS) near8 (silane or "SH. sub.4"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:32
S64	1	(epitaxial near4 reactor near4 chamber) same (mixture near8 (chlorosilane or dichlorosilane or trichlorosilane or tetrachlorosilane or DCS) near8 (silane or "SH. sub.4"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/04 09:33
S65	2	("6184154").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/14 10:49
S66	206100	(Silane or "SH.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:15
S67	986025	dichlorosilane or dichloro-silane or DCS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:16
S68	195485	phosphorous or phosphine or "PH. sub.3"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17
S69	181769	(inert or purge or purged) near8 (nitrogen or "N.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17

S70	1171	S66 and S67 and S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:17
S71	21	S66 same S67 same S68 same S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:18
S72	5117937	(silicon or Si or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:20
S73	21	S71 and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:20
S74	11	S73 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:21
S75	1411	n-type near8 silicon near8 (phosphine or phosphorous or "PH. sub.3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:24
S76	10	S75 and (epitaxial near reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:27
S77	2	("6184154").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/14 13:49
S78	8	("20030003646" "5378651" "6251188" "6391749").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:01
S79	2	S78 and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:47
S80	6646	S66 same S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:48

S81	42	S80 and MOSFET and (elevated near4 source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:49
S82	10	S81 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:50
S83	1	S82 and (bipolar near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:52
S84	51	S80 and (bipolar near transistor) and (base near region) and (emitter near region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:53
S85	49	S84 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:53
S86	29	S85 and (epitaxial near4 (grow or growing or growth))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:54
S87	14	S86 and pnp	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:55
S88	469	(epitaxial\$4 near8 (grow or growed or growing or growth)) near8 (base near8 emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:58
S89	5	S85 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:59
S90	5	S89 and n-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 14:59
S91	1610	Alonso.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:26

S92	2	S91 and (epitaxial near8 growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:27
S93	2	S91 and (epitaxial near8 growth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 15:28
S94	2	(phosphorous near8 n-type) near8 (epitaxial near8 source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/15 09:10
Si06	40	(epitaxial near reactor) near8 LPCVD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 16:59
Si07	12	MOSFET and (raised near8 source/ drain) and (epitaxial near reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:02
Si08	5	Si07 and ((@ad<"20030328") or (@rlad<"20030328"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:04
Si09	3	MOSFET and ((epitaxial near8 (raised near4 source/drain)) same reactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/16 17:30

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